

SURFACE MOUNT ULTRA LOW LEAKAGE SILICON SWITCHING DIODES



V<sub>R</sub>=0, f=1.0MHz

 $I_R=I_F=10mA$ ,  $I_{rr}=1.0mA$ ,  $R_L=100\Omega$ 

CT

t<sub>rr</sub>

• Device is *Halogen Free* by design

**Central** Semiconductor Corp.

www.centralsemi.com

### DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMSD6001 SERIES are silicon switching diodes manufactured by the epitaxial planar process, epoxy molded in a SUPERmini<sup>™</sup> surface mount package, designed for switching applications requiring an extremely low leakage diode.

2.0

3.0

MAXIMUM RATINGS: $(T_A=25^{\circ}C)$ SYMBOLUNITSContinuous Reverse Voltage $V_R$ 75 $V$ Peak Repetitive Reverse Voltage $V_{RRM}$ 100 $V$ Continuous Forward Current $I_F$ 250mAPeak Repetitive Forward Current $I_{FRM}$ 250mAPeak Forward Surge Current, tp=1.0µs $I_{FSM}$ 4.0APeak Forward Surge Current, tp=1.0s $I_{FSM}$ 1.0APower Dissipation $P_D$ 275mWOperating and Storage Junction Temperature $T_{I_L}T_{stg}$ -65 to +150°C	CMSD6001	: SINGLE A: DUAL, COMMON ANODE C: DUAL, COMMON CATHODE S: DUAL, IN-SERIES	MARKING COI MARKING COI MARKING COI MARKING COI	DE: 61A DE: 61C	
Peak Repetitive Reverse VoltageV VRRM100VContinuous Forward CurrentIF250mAPeak Repetitive Forward CurrentIFRM250mAPeak Forward Surge Current, tp=1.0µsIFSM4.0APeak Forward Surge Current, tp=1.0sIFSM1.0APower DissipationPD275mW			SYMBOL		
Continuous Forward CurrentIF250mAPeak Repetitive Forward CurrentIFRM250mAPeak Forward Surge Current, tp=1.0µsIFSM4.0APeak Forward Surge Current, tp=1.0sIFSM1.0APower DissipationPD275mW	Continuous F	Reverse Voltage	VR	75	V
Peak Repetitive Forward CurrentIFRM250mAPeak Forward Surge Current, tp=1.0µsIFSM4.0APeak Forward Surge Current, tp=1.0sIFSM1.0APower DissipationPD275mW	Peak Repetit	ive Reverse Voltage	V <sub>RRM</sub>	100	V
Peak Forward Surge Current, tp=1.0µsIFSM4.0APeak Forward Surge Current, tp=1.0sIFSM1.0APower DissipationPD275mW	Continuous Forward Current		۱ <sub>F</sub>	250	mA
Peak Forward Surge Current, tp=1.0sI FSM1.0APower DissipationPD275mW	Peak Repetit	ive Forward Current	IFRM	250	mA
Power Dissipation PD 275 mW	Peak Forward	d Surge Current, tp=1.0µs	IFSM	4.0	А
	Peak Forward	Peak Forward Surge Current, tp=1.0s		1.0	А
Operating and Storage Junction Temperature T <sub>1</sub> , T <sub>sto</sub> -65 to +150 °C	Power Dissip	pation	PD	275	mW
1 C C 1 0/ 3tg	Operating an	d Storage Junction Temperature	т <sub>Ј</sub> , т <sub>stg</sub>	-65 to +150	°C
Thermal Resistance $\Theta_{JA}$ 455 °C/W	Thermal Resistance		$\Theta_{JA}$	455	°C/W
ELECTRICAL CHARACTERISTICS PER DIODE: (T <sub>A</sub> =25°C unless otherwise noted)					
SYMBOL TEST CONDITIONS MIN MAX UNITS					UNITS
I <sub>R</sub> V <sub>R</sub> =75V 500 pA	IR	V <sub>R</sub> =75V		500	pA
BV <sub>R</sub> I <sub>R</sub> =100μA 100 V	BVR	I <sub>R</sub> =100μA	100		V
V <sub>F</sub> I <sub>F</sub> =1.0mA 0.85 V	V <sub>F</sub>	I <sub>F</sub> =1.0mA		0.85	V
V <sub>F</sub> I <sub>F</sub> =10mA 0.95 V	V <sub>F</sub>	I <sub>F</sub> =10mA		0.95	V
V <sub>F</sub> I <sub>F</sub> =100mA 1.1 V	VF	I <sub>F</sub> =100mA		1.1	V

R3 (9-May 2011)

pF

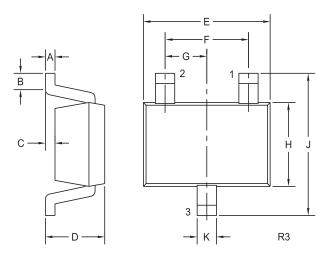
μs





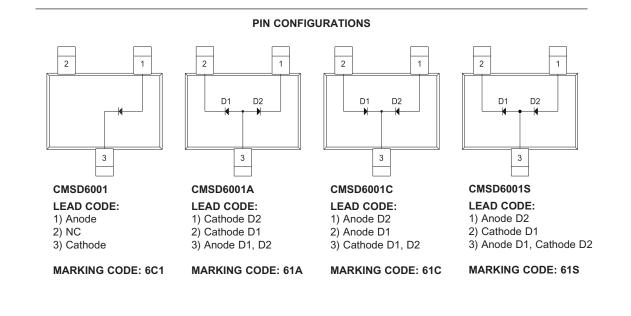
#### SURFACE MOUNT ULTRA LOW LEAKAGE SILICON SWITCHING DIODES

#### SOT-323 CASE - MECHANICAL OUTLINE



DIMENSIONS								
	INCHES		MILLIMETERS					
SYMBOL	MIN	MAX	MIN	MAX				
А	0.002	0.008	0.05	0.20				
В	0.004	-	0.10	-				
С	-	0.004	-	0.10				
D	0.031	0.043	0.80	1.10				
E	0.071	0.087	1.80	2.20				
F	0.051		1.30					
G	0.026		0.65					
Н	0.045	0.053	1.15	1.35				
J	0.079	0.087	2.00	2.20				
K	0.008	0.016	0.20	0.40				
SOT-323 (REV/· R3)								

SOT-323 (REV: R3)



R3 (9-May 2011)

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# OUTSTANDING SUPPORT AND SUPERIOR SERVICES



### PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options

## DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2<sup>nd</sup> day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities

Special wafer diffusions

· Custom product packing

- PbSn plating options
- Package details
- Application notes
- · Application and design sample kits

· Custom bar coding for shipments

Custom product and package development

#### REQUESTING PRODUCT PLATING

- 1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
- 2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

#### CONTACT US

#### Corporate Headquarters & Customer Support Team

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